

UPDATED 08/21/2007

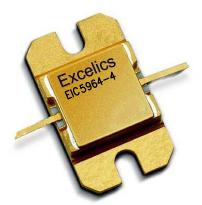
5.90-6.40 GHz 4-Watt Internally Matched Power FET

FEATURES

- 5.90–6.40GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +36.5 dBm Output Power at 1dB Compression

FI ECTRICAL CHARACTERISTICS (T. = 25^{\circ}C)

- 10.0 dB Power Gain at 1dB Compression
- 37% Power Added Efficiency
- -46 dBc IM3 at PO = 25.5 dBm SCL
- 100% Tested for DC, RF, and R_{TH}



EIC5964-4

Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	ТҮР	MAX	UNITS		
P _{1dB}	Output Power at 1dB Compression $f = 5.90-6.40$ GHz V _{DS} = 10 V, I _{DSQ} ≈ 1100mA	35.5	36.5		dBm		
G _{1dB}	Gain at 1dB Compressionf = 5.90-6.40GHz V_{DS} = 10 V, $I_{DSQ} \approx$ 1100mA	9.0	10.0		dB		
∆G	Gain Flatnessf = 5.90-6.40GHz V_{DS} = 10 V, $I_{DSQ} \approx$ 1100mA			±0.6	dB		
PAE	Power Added Efficiency at 1dB Compression V_{DS} = 10 V, $I_{DSQ} \approx$ 1100mAf = 5.90-6.40GHz		37		%		
Id _{1dB}	Drain Current at 1dB Compression f = 5.90-6.40GHz		1100	1300	mA		
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; Pout = 25.5 dBm S.C.L ² V_{DS} = 10 V, $I_{DSQ} \approx 65\%$ IDSSf = 6.40GHz	-43	-46		dBc		
I _{DSS}	Saturated Drain Current $V_{DS} = 3 V, V_{GS} = 0 V$		2000	2500	mA		
VP	Pinch-off Voltage V_{DS} = 3 V, I_{DS} = 20 mA		-2.5	-4.0	V		
R _{TH}	Thermal Resistance ³		5.5	6.0	°C/W		

Note: 1. Tested with 100 Ohm gate resistor.

2. S.C.L. = Single Carrier Level.

3. Overall Rth depends on case mounting.

ABSOLUTE MAXIMUM RATING FOR EFE

SYMBOLS	PARAMETERS			
Vds	Drain-Source Voltage	15V	10V	
Vgs	Gate-Source Voltage	-5V	-4V	
lgf	Igf Forward Gate Current		14.4mA	
lgr	Reverse Gate Current	-9.6mA	-2.4mA	
Pin	Input Power	36dBm	@ 3dB Compression	
Tch	Channel Temperature	175C	175C	
Tstg	Tstg Storage Temperature		-65C to +175C	
Pt	Pt Total Power Dissipation		25W	

te: 1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.

Specifications are subject to change without notice. Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085 Phone: 408-737-1711 Fax: 408-737-1868 Web: <u>www.excelics.com</u>

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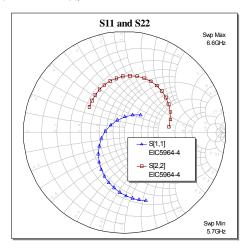
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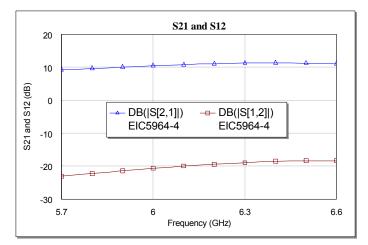
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PERFORMANCE DATA

Typical S-Parameters (T= 25°C, 50 Ω system, de-embedded to edge of package) V_{DS} = 10 V, I_{DSQ} ≈ 1100mA





FREQ	S11		S21		\$12		\$22	
(GHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
5.7	0.708	-72.6	2.878	22.3	0.070	-35.4	0.429	143.7
5.8	0.657	-82.8	3.031	9.4	0.077	-49.8	0.471	127.6
5.9	0.596	-94.2	3.191	-4.3	0.085	-62.3	0.512	112.8
6.0	0.521	-107.1	3.328	-18.3	0.093	-76.6	0.543	98.4
6.1	0.433	-122.1	3.465	-33.0	0.101	-91.6	0.565	84.4
6.2	0.336	-140.5	3.584	-48.4	0.107	-106.3	0.574	70.0
6.3	0.234	-166.0	3.658	-64.1	0.113	-121.2	0.565	55.4
6.4	0.155	151.6	3.675	-80.0	0.119	-138.1	0.540	40.2
6.5	0.156	88.5	3.648	-96.2	0.120	-154.0	0.500	24.2
6.6	0.236	47.4	3.543	-112.3	0.121	-169.8	0.444	7.4

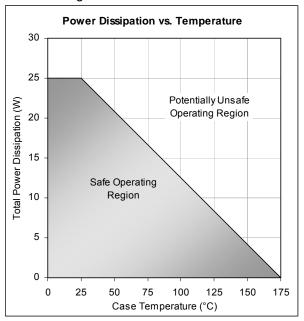


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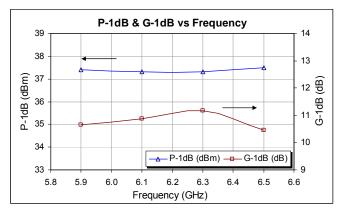
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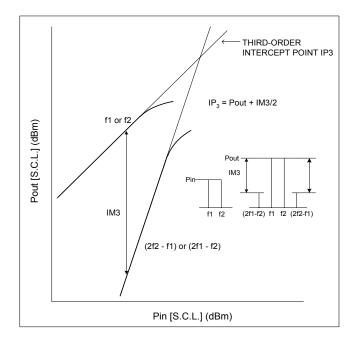
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Power De-rating Curve and IM3 Definition

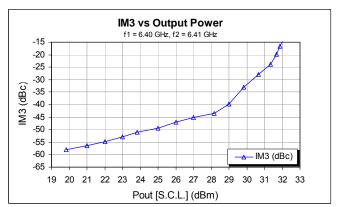


Typical Power Data (V_{DS} = 10 V, I_{DSQ} = 1100 mA)





Typical IM3 Data (V_{DS} = 10 V, I_{DSQ} \approx 65\% IDSS)





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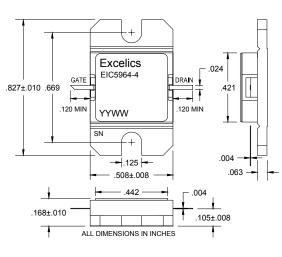
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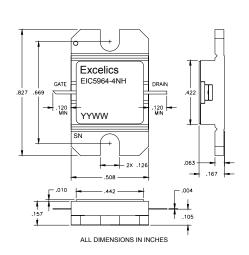
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PACKAGES OUTLINE

Dimensions in inches, Tolerance + .005 unless otherwise specified

EIC5964-4 (Hermetic)





EIC5964-4NH (Non-Hermetic)



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ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC5964-4	Hermetic	Industrial	5.90-6.40GHz	35.5	-43
EIC5964-4NH	Non-Hermetic	Industrial	5.90-6.40GHz	35.5	-43

Notes: 1. Contact factory for military and hi-rel grades.

2. Exact test conditions are specified in "Electrical Characteristics" table.

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness